VS-P400 Series

RoHS COMPLIANT



Power Modules, Passivated Assembled Circuit Elements, 40 A



www.vishay.com

PACE-PAK (D-19)

PRIMARY CHARACTERISTICS					
Io	40 A				
Туре	Modules - thyristor, standard				
Package	PACE-PAK (D-19)				

FEATURES

- · Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 $V_{\text{RRM}}/V_{\text{DRM}}$
- High dynamic characteristics
- · Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-P400 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS VALUES		UNITS				
I _O	80 °C	40	А				
I _{TSM} ,	50 Hz	385	А				
I _{FSM}	60 Hz	400	A				
l ² t	50 Hz	745	A ² s				
1-1	60 Hz	680	A-5				
l²√t		7450	A²√s				
V _{RRM}	Range	400 to 1200	V				
V _{ISOL}		2500	V				
TJ		-40 to +125	°C				
T _{Stg}		-40 10 +123	U				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND PEAK OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J MAXIMUM mA			
VS-P401, VS-P421, VS-P431	400	500				
VS-P402, VS-P422, VS-P432	600	700				
VS-P403, VS-P423, VS-P433	S-P403, VS-P423, VS-P433 800		10			
VS-P404, VS-P424, VS-P434	1000	1100				
VS-P405, VS-P425, VS-P435	1200	1300				

Revision: 27-Jul-2018 1 Document Number: 93755 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





Vishay Semiconductors

PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS
Maximum DC output current		Evel la vial era				А
at case temperature	Ι _Ο	Full bridge	CIrcuits		80	°C
		t = 10 ms	No voltage		385	
Maximum peak, one-cycle	I _{TSM} ,	t = 8.3 ms	reapplied		400	А
non-repetitive on-state or forward current	I _{FSM}	t = 10 ms	100 % V _{RRM}		325	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	340	
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	745	
Maximum I ² t for fusing	l ² t	t = 8.3 ms		-	680	A ² s
		t = 10 ms	100 % V _{BBM}		530	
		t = 8.3 ms	reapplied		480	
Maximum $I^2 \sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied I ² t for time tx = I ² $\sqrt{t} \cdot \sqrt{tx}$			7450	A²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.83	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), T _J = T _J maxim	านm	1.03	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	: x I _{T(AV)} < I < π x	$I_{T(AV)}$), $T_J = T_J$ maximum	9.61	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		7.01	1112.2	
Maximum on-state voltage drop	V _{TM}	$I_{TM} = \pi \times I_{T(AV)}$ $T_J = 25 \text{ °C}$		T _J = 25 °C	1.4	V
Maximum forward voltage drop	V _{FM}	$I_{FM} = \pi \times I_{F(AV)}$ $T_J = 25 \text{ °C}$		T _J = 25 °C	1.4	V
Maximum non-repetitive rate of rise of turned-on current	dl/dt	T _J = 125 °C from 0.67 V _{DRM} I _{TM} = π x I _{T(AV)} , I _g = 500 mA, t _r < 0.5 μs, t _p > 6 μs		200	A/µs	
Maximum holding current	Ι _Η	т об ос		C.V. registive lood	130	
Maximum latching current	١L	$T_J = 25 \text{ °C}$ anode supply = 6 V, resistive load		250	mA	

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, exponential to 0.67 V_{DRM} gate open	200	V/µs		
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM} , I _{DRM}	$I_1 = 125$ G, gate open circuit		mA		
Maximum peak reverse leakage current	I _{RRM}	T _J = 25 °C	100	μA		
RMS isolation voltage	V _{ISOL}	50 Hz, circuit to base, all terminals shorted, T_J = 25 °C, t = 1 s	2500	V		

TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			8	W
Maximum average gate power	P _{G(AV)}			2	vv
Maximum peak gate current	I _{GM}			2	А
Maximum peak negative gate voltage	-V _{GM}			10	V
Maximum gate voltage required to trigger	V _{GT}	T _J = - 40 °C	Anode supply = 6 V resistive load	3	V
		T _J = 25 °C		2	
		T _J = 125 °C		1	
		T _J = - 40 °C		90	mA
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C		60	
		T _J = 125 °C		35	
Maximum gate voltage that will not trigger	V _{GD}	T ₁ = 125 °C, rated V _{DBM} applied		0.2	V
Maximum gate current that will not trigger	I _{GD}			2	mA

Document Number: 93755

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-P400 Series



Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
Maximum junction operating and storage temperature range	T _J , T _{Stg}		-40 to +125	°C	
Maximum thermal resistance, junction to case per junction	R _{thJC}	R _{thJC} DC operation		K/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.10	r./ vv	
Mounting torque, base to heatsink ⁽¹⁾			4	Nm	
Approximate weight			58	g	
			2.0	oz.	
Case style			PACE-PAK (D-19)		

Note

⁽¹⁾ A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

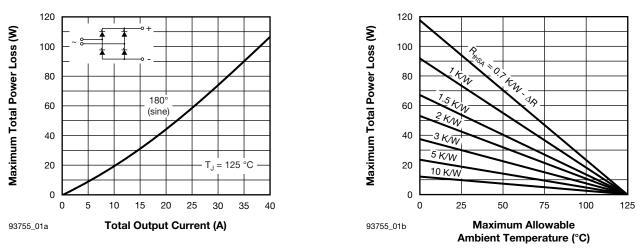
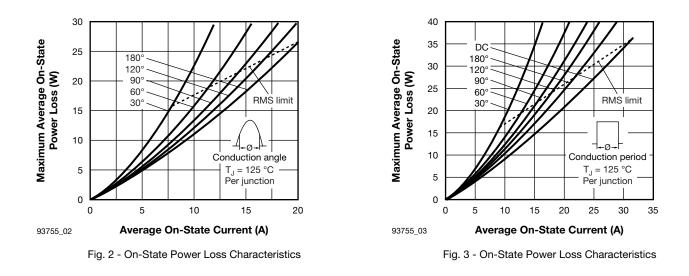


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)



3

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay Semiconductors

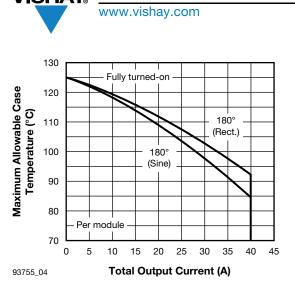


Fig. 4 - Current Ratings Characteristics

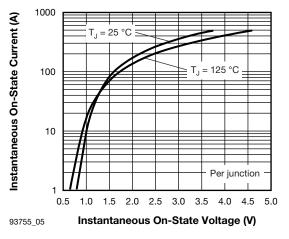


Fig. 5 - On-State Voltage Drop Characteristics

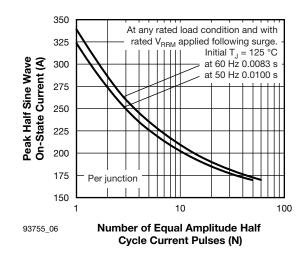
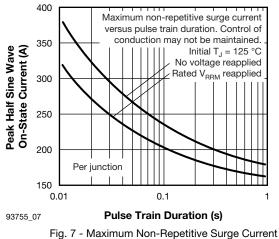
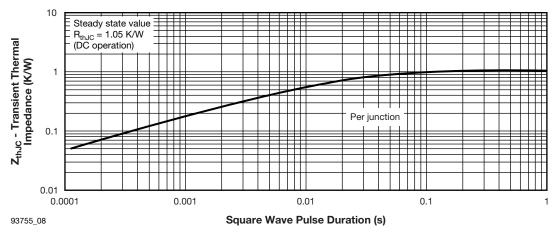
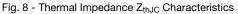


Fig. 6 - Maximum Non-Repetitive Surge Current









Revision: 27-Jul-2018 Document Number: 93755 4 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

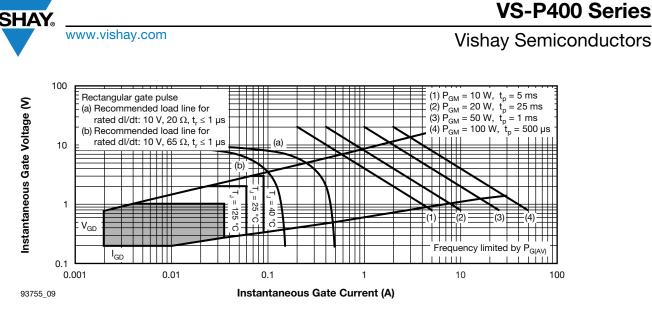


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	Р	4	0	2	к	w	
	1	2	3	4	5	6	7	I
	1 2 3 4	- Mo - Cur 1 = 4 = - Circ 0 = 2 =	dule typ rrent rati 25 A D0 40 A D0 cuit cont single p single p	ng C (P100 C (P400 figuratio bhase, h	series) series) n ybrid br ybrid br	idge coi		athode
	5	1 = 2 = 3 = 4 =	tage coo 400 V 600 V 800 V 1000 V 1200 V	de				
	6		-	al voltage al freewl				



www.vishay.com

Vishay Semiconductors

CIRCUIT CONFIGUR	CIRCUIT CONFIGURATION				
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	SCHEMATIC DIAGRAM	TERMINAL POSITIONS		
Single phase, hybrid bridge common cathode	0	(-) $(-)$ $(+)$ $(+)$ $(+)$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		
Single phase, hybrid bridge doubler connection	2	$G1 \circ G2$ AC2 $AC1 \circ$ (-) $C1 \circ C(+)$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		
Single phase, all SCR bridge	3	G^{3} G^{3} G^{1} AC10 AC20 G^{4} G^{2} $(+)$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		

CODING ⁽¹⁾								
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	BASIC SERIES	WITH VOLTAGE SUPPRESSION	WITH FREEWHEELING DIODE	WITH BOTH VOLTAGE SUPPRESSION AND FREEWHEELING DIODE			
Single phase, hybrid bridge common cathode	0	P40.	P40.K	P40.W	P40.KW			
Single phase, hybrid bridge doubler connection	2	P42.	P42.K	-	-			
Single phase, all SCR bridge	3	P43.	P43.K	-	-			

Note

⁽¹⁾ To complete code refer to Voltage Ratings table, i.e.: for 600 V P40.W complete code is P402W

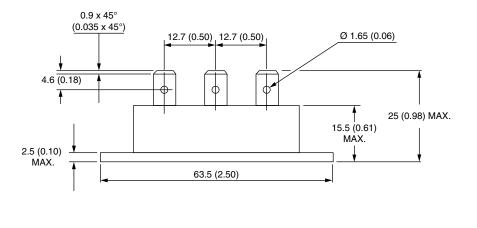
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95335			

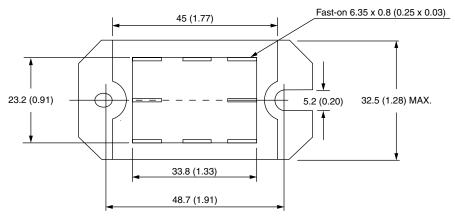
Vishay Semiconductors

D-19 PACE-PAK

DIMENSIONS in millimeters (inches)

SHA







Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.